MOS FET

FL5252050R

Panasonic

FL5252050R

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

■ Features

- Low drain-source ON resistance : RDS (on) typ. = 100 m Ω (VGS = -4.0 V)
- Low drive voltage : 2.5 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: Y0

Established: 2011-06-17

: 2013-10-28

Revised

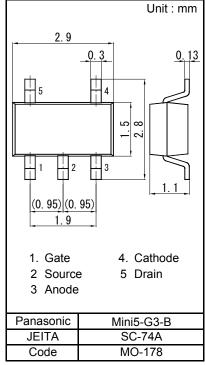
■ Packaging

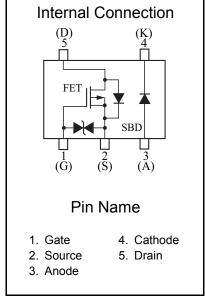
Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

項目		Symbol	Rating	Unit	
FET	Drain to Source Voltage	VDS	-20	V	
	Gate to Source Voltage	VGS	±10	V	
	Drain current	ID	-2.1	Α	
	Drain Current (Pulsed)	IDp	-8	Α	
	Channel temperature	Tch	125	°C	
SBD	Reverse voltage	VR	20	V	
	Forward current (Average)	IF(AV)	700	mA	
	Junction temperature	Tj	125	°C	
Overall	Total power dissipation *1	PD	600	mW	
	Operating ambient temperature	Topr	-40 to + 85	°C	
	Storage temperature	Tstg	-55 to +125	°C	

Note: *1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.1 mm
PD absolute maximum rating without a heat shink: 300 mW





Panasonic

MOS FET

FL5252050R

■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain to Source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0			-1.0	μA
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, \text{ VDS} = 0$			±10	μA
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10 V	-0.4	-0.85	-1.3	V
Drain-source On-State Resistance	RDS(on)1	ID = -1.0 A, VGS = -4.0 V		100	130	mΩ
Dialii-source Oil-State Resistance	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		130	200	1112.2
Forward transfer admittance	Yfs	ID = -1.0 A, VDS = -10 V	3.0			S
Input Capacitance	Ciss			400		pF
Output Capacitance	Coss	VDS = -10 V, VGS = 0, f = 1 MHz		40		pF
Reverse Transfer Capacitance C]		35		pF
Turn-on time ^{*1}	ton	VDD = -10 V, VGS = 0 to -4 V ID = -1.0 A		35		ns
Turn-off time ^{*1}	toff	VDD = -10 V, VGS = -4 to 0 V ID = -1.0 A		100		ns

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 700 mA			0.45	V
Reverse current	IR	VR = 20 V			200	μA
Terminal capacitance	Ct	VR = 10 V, f = 1 MHz		12		pF
Reverse recovery time	trr	IF = IR = 100 mA, Irr = 10 mA		4.3		ns

Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

Established: 2011-06-17 : 2013-10-28 Revised

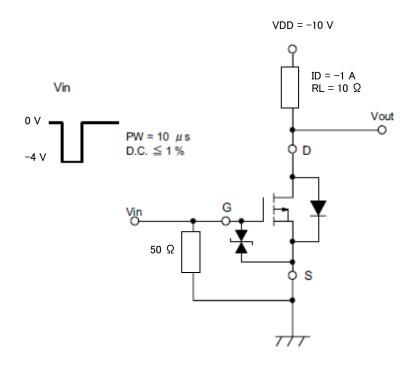
^{2. *1} Turn-on, Turn-off measurement circuit

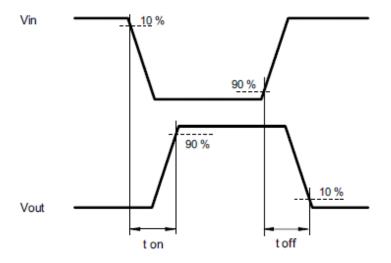
MOS FET

FL5252050R

Panasonic

*1 Turn-on, Turn-off measurement circuit





Page 3 of 6

Revision. 3

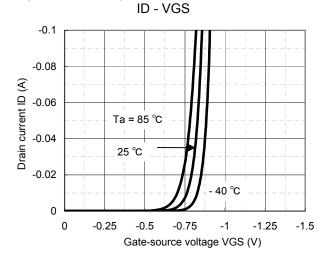
MOS FET

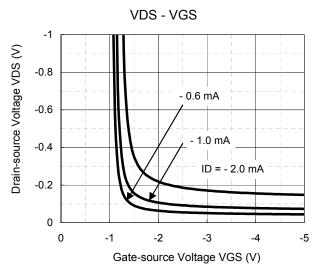
FL5252050R

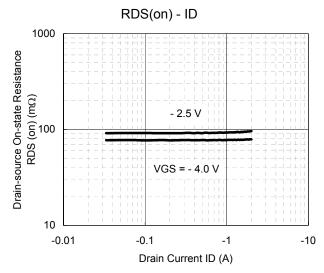
Panasonic

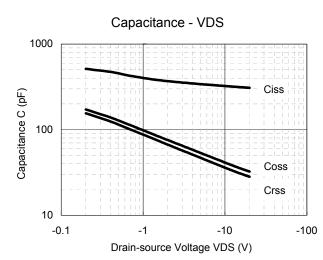
Technical Data (reference)

ID - VDS -2 - 4.0 V 2.0 V -1.5 Drain current ID (A) VGS = - 1.5 V -1 -0.5 - 1.0 V 0 0 -0.1 -0.2 -0.3 -0.4 -0.5 -0.6 Drain-source voltage VDS (V)







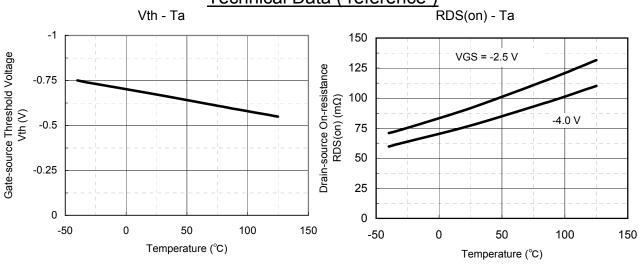


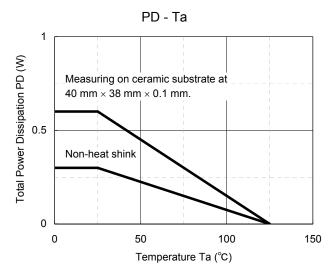
Panasonic

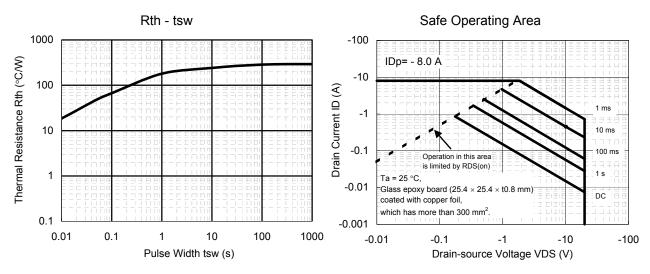
MOS FET

FL5252050R









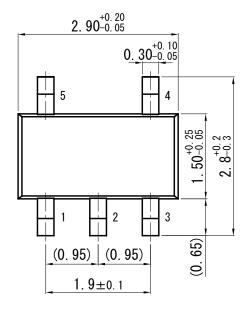
MOS FET

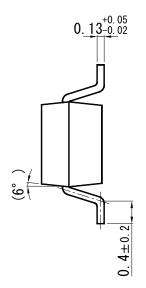
FL5252050R

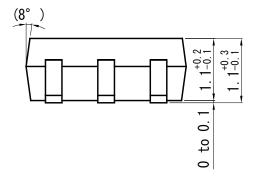
Mini5-G3-B

Panasonic

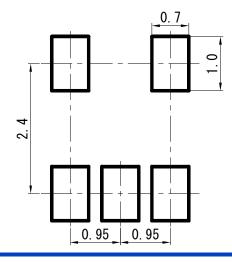
Unit: mm







■ Land Pattern (Reference) (Unit: mm)



Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for general applications (such as office equipment, communications equipment, measuring instruments and household appliances), or for specific applications as expressly stated in this book.

 Consult our sales staff in advance for information on the following applications:
 - Special applications (such as for airplanes, aerospace, automotive equipment, traffic signaling equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - It is to be understood that our company shall not be held responsible for any damage incurred as a result of or in connection with your using the products described in this book for any special application, unless our company agrees to your using the products in this book for any special application.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of our company.

20100202